

IPD78CN10NGBUMA1

IPD78CN10NGBUMA1 Information



For Reference Only

Part Number IPD78CN10NGBUMA1 **Manufacturer** Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 100V 13A TO252-3 **Package** TO-252-3, DPak (2 Leads + Tab), SC-63

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IPD78CN10NGBUMA1 Specifications

Manufacturer Part Number IPD78CN10NGBUMA1 Manufacturer Infineon Technologies Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-252-3, DPak (2 Leads + Tab), SC-63 Series OptiMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 13A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 12μA Gate Charge (Qg) (Max) @ Vgs 11nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 716pF @ 50V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 31W (Tc) Rds On (Max) @ Id, Vgs 78 mOhm @ 13A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO252-3 Technology To School All Colon and The Technology		
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Series OptiMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 13A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 12µA Gate Charge (Qg) (Max) @ Vgs 11nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 716pF @ 50V Vgs (Max) ±20V FET Feature Power Dissipation (Max) 31W (Tc) Rds On (Max) @ Id, Vgs 78 mOhm @ 13A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO252-3		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C13A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 12μAGate Charge (Qg) (Max) @ Vgs11nC @ 10VInput Capacitance (Ciss) (Max) @ Vds716pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)31W (Tc)Rds On (Max) @ Id, Vgs78 mOhm @ 13A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackagePG-TO252-3	Package	TO-252-3, DPak (2 Leads + Tab), SC-63
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Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 12μAGate Charge (Qg) (Max) @ Vgs11nC @ 10VInput Capacitance (Ciss) (Max) @ Vds716pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)31W (Tc)Rds On (Max) @ Id, Vgs78 mOhm @ 13A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackagePG-TO252-3	Drain to Source Voltage (Vdss)	100V
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Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package 716pF @ 50V **20V **20V **31W (Tc) **31W (Tc) 78 mOhm @ 13A, 10V -55°C ~ 175°C (TJ) Surface Mount PG-TO252-3	Vgs(th) (Max) @ Id	4V @ 12μA
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FET Feature - Power Dissipation (Max) 31W (Tc) Rds On (Max) @ Id, Vgs 78 mOhm @ 13A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO252-3	Input Capacitance (Ciss) (Max) @ Vds	716pF @ 50V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 78 mOhm @ 13A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO252-3	Vgs (Max)	±20V
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Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO252-3	Power Dissipation (Max)	31W (Tc)
Mounting Type Surface Mount Supplier Device Package PG-TO252-3	Rds On (Max) @ Id, Vgs	78 mOhm @ 13A, 10V
Supplier Device Package PG-TO252-3	Operating Temperature	-55°C ~ 175°C (TJ)
••	Mounting Type	Surface Mount
TO 252.2 DD-1-(211-) TC 25	Supplier Device Package	PG-TO252-3
Package / Case 10-252-5, DPak (2 Leads + 1ab), SC-65	Package / Case	TO-252-3, DPak (2 Leads + Tab), SC-63
Report errors?		Report errors?

IPD78CN10NGBUMA1 Guarantees



Ouality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IPD78CN10NGBUMA1 Payment Methods



















IPD78CN10NGBUMA1 Shipping Methods













If you have any question about IPD78CN10NGBUMA1, please do not hesitate to contact us!

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